

What is claimed is:

1. A mask pattern for sequential lateral solidification (SLS) comprising:

- 5 a) a first set of slits for achieving a first two-shot SLS process; and
- b) a second set of slits at a desired angle relative to the first set of slits for achieving a second two-shot SLS process.

2. The mask pattern of claim 1, wherein the desired angle is 90 degrees.

10 3. The mask pattern of claim 1, wherein the first set of slits further comprises:

- a) a first array of beamlets for projecting a first pattern; and
- b) a second array of beamlets adjacent to the first array
- 15 of beamlets and offset such that the second array of beamlets are aligned with the gaps between the first array of beamlets, whereby the first array of beamlets and the second array of beamlets can be used in combination in a two shot SLS process.

20 4. The mask pattern of claim 3, wherein the second set of slits further comprises:

- a) a third array of beamlets aligned at a 90 degree angle relative to the first array of beamlets and the second array of beamlets; and

b) a forth array of beamlets parallel and adjacent to the
25 third array of beamlets adjacent and separated by a gap that is wider
than a space between adjacent individual beamlets, whereby the third
array of beamlets and the forth array of beamlets can be used in
combination in a two shot SLS process.

5. A method of crystallizing a thin film of material
30 comprising the steps of:

- a) depositing a thin film of material over a substrate;
- b) irradiating regions of the material with a first array of
beamlets by positioning a mask comprising the pattern of the first array of
beamlets over the regions;
- 35 c) stepping the mask until a second array of beamlets is
positioned at least partially overlapping the regions irradiate by the first
array of beamlets;
- d) irradiating regions adjacent to the regions irradiated
by the first array of beamlets;
- 40 e) stepping the mask until a third array of beamlets is
positioned at least partially overlapping the regions irradiated by the first
array of beamlets and the second array of beamlets;
- f) irradiating regions of the material with the third array
of beamlets;
- 45 g) stepping the mask until a forth array of beamlets is
positioned at least partially overlap regions of the material irradiated by
the third array of beamlets; and
- h) irradiating regions adjacent to the regions irradiated
by the third array of beamlets.

50 6. The method of claim 5, wherein the mask is not
rotated relative to the material during processing.

 7. A method of performing a 2 + 2 process on a material
layer deposited over a substrate comprising the steps of:

 a) providing a mask comprising a first set of
55 substantially parallel slits and a second set of substantially parallel slits
at an angle relative to the first set of slits;

 b) performing a first 2-shot process using the first set of
slits;

 c) translating the mask laterally; and

60 d) performing a second 2-shot process using the second
set of slits.

 8. The method of claim 7, wherein the mask is translated
laterally without rotating the substrate relative to the mask.

 9. The method of claim 7, wherein the second set of
65 substantially parallel slits is at an approximately 90 degree angle relative
to the first set of slits.

 10. The method of claim 7, wherein the first set of slits
comprises a first array of beamlets and a second array of beamlets, and
the step of performing the first 2-shot process further comprises the steps
70 of:

 a) irradiating the material layer through the first array
of beamlets to crystallize a first set of material regions;

b) translating the mask laterally; and
c) irradiating the material layer through the second
75 array of beamlets to crystallize regions of the material layer adjacent to
the first set of material regions.

11. The method of claim 10, wherein the second set of
slits comprises comprises a third array of beamlets and a forth array of
beamlets, and the step of performing the second 2-shot process further
80 comprises the steps of:
a) irradiating the material layer through the third array
of beamlets to recrystallize regions of material;
b) translating the mask laterally; and
c) irradiating the material layer through the forth array
85 of beamlets to crystallize regions of the material layer adjacent to the
material crystallize by the third set of beamlets.